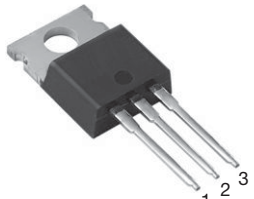
High Voltage, Phase Control Thyristor, 12 A



TO-220AB

FEATURES

- AEC-Q101 qualified
- Meets JESD 201 class 1A whisker test
- Flexible solution for reliable AC power rectification
- Easy control peak current at charger power up to reduce passive / electromechanical components
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912

RoHS COMPLIANT
HALOGEN FREE

APPLICATIONS

- On-board and off-board EV / HEV battery chargers
- Renewable energy inverters

DESCRIPTION

The VS-12TTS08HM3 high voltage series of silicon controlled rectifiers are specifically designed for medium power switching and phase control applications.

PRIMARY CHARACTERISTICS	
$I_{T(AV)}$	8 A
V_{DRM}/V_{RRM}	800 V
V_{TM}	1.2 V
I_{GT}	15 mA
T_J	-40 to +125 °C
Package	TO-220AB
Circuit configuration	Single SCR

OUTPUT CURRENT IN TYPICAL APPLICATIONS			
APPLICATIONS	SINGLE-PHASE BRIDGE	THREE-PHASE BRIDGE	UNITS
Capacitive input filter T_A = 55 °C, T_J = 125 °C, common heatsink of 1 °C/W	13.5	17	A

MAJOR RATINGS AND CHARACTERISTICS			
PARAMETER	TEST CONDITIONS	VALUES	UNITS
$I_{T(AV)}$	Sinusoidal waveform	8	A
$I_{T(RMS)}$		12.5	
V_{RRM}/V_{DRM}		800	V
I_{TSM}		110	A
V_T	8 A, T_J = 25 °C	1.2	V
dV/dt		150	V/µs
dI/dt		100	A/µs
T_J	Range	-40 to +125	°C

VOLTAGE RATINGS			
PART NUMBER	V_{RRM}, MAXIMUM PEAK REVERSE VOLTAGE V	V_{DRM}, MAXIMUM PEAK DIRECT VOLTAGE V	I_{RRM} / I_{DRM} AT 125 °C mA
VS-12TTS08HM3	800	800	5.0

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	**SYMBOL**	**TEST CONDITIONS**		**VALUES**	**UNITS**
Maximum average on-state current	$I_{T(AV)}$	T_C = 108 °C, 180° conduction, half sine wave		8	A
Maximum RMS on-state current	$I_{T(RMS)}$			12.5	
Maximum peak one-cycle non-repetitive surge current	I_{TSM}	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C		95	
		10 ms sine pulse, no voltage reapplied, T_J = 125 °C		110	
Maximum I^2t for fusing	I^2t	10 ms sine pulse, rated V_{RRM} applied, T_J = 125 °C		45	A^2s
		10 ms sine pulse, no voltage reapplied, T_J = 125 °C		64	
Maximum $I^2\sqrt{t}$ for fusing	$I^2\sqrt{t}$	t = 0.1 ms to 10 ms, no voltage reapplied, T_J = 125 °C		640	$A^2\sqrt{s}$
Maximum on-state voltage drop	V_{TM}	8 A, T_J = 25 °C		1.2	V
On-state slope resistance	r_t	T_J = 125 °C		16.2	mΩ
Threshold voltage	$V_{T(TO)}$			0.87	V
Maximum reverse and direct leakage current	I_{RM}/I_{DM}	T_J = 25 °C	V_R = rated V_{RRM} / V_{DRM}	0.05	mA
		T_J = 125 °C		5.0	
Typical holding current	I_H	Anode supply = 6 V, resistive load, initial I_T = 1 A, T_J = 25 °C		30	
Typical latching current	I_L	Anode supply = 6 V, resistive load, T_J = 25 °C		50	
Maximum rate of rise of off-state voltage	dV/dt	T_J = T_J max., linear to 80 %, V_{DRM} = R_g - k = open		150	V/µs
Maximum rate of rise of turned-on current	dI/dt			100	A/µs

TRIGGERING				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum peak gate power	P_{GM}		8.0	W
Maximum average gate power	$P_{G(AV)}$		2.0	
Maximum peak positive gate current	$+I_{GM}$		1.5	A
Maximum peak negative gate voltage	$-V_{GM}$		10	V
Maximum required DC gate current to trigger	I_{GT}	Anode supply = 6 V, resistive load, T_J = - 65 °C	20	mA
		Anode supply = 6 V, resistive load, T_J = 25 °C	15	
		Anode supply = 6 V, resistive load, T_J = 125 °C	10	
Maximum required DC gate voltage to trigger	V_{GT}	Anode supply = 6 V, resistive load, T_J = -65 °C	1.2	V
		Anode supply = 6 V, resistive load, T_J = 25 °C	1	
		Anode supply = 6 V, resistive load, T_J = 125 °C	0.7	
Maximum DC gate voltage not to trigger	V_{GD}	T_J = 125 °C, V_{DRM} = rated value	0.2	
Maximum DC gate current not to trigger	I_{GD}		0.1	mA

SWITCHING				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Typical turn-on time	t_{gt}	T_J = 25 °C	0.8	µs
Typical reverse recovery time	t_{rr}	T_J = 125 °C	3	
Typical turn-off time	t_q		100	

THERMAL AND MECHANICAL SPECIFICATIONS				
PARAMETER	**SYMBOL**	**TEST CONDITIONS**	**VALUES**	**UNITS**
Maximum junction and storage temperature range	T_J, T_{Stg}		-40 to +125	°C
Maximum thermal resistance, junction to case	R_{thJC}	DC operation	1.5	°C/W
Maximum thermal resistance, junction to ambient	R_{thJA}		62	
Typical thermal resistance, case to heatsink	R_{thCS}	Mounting surface, smooth, and greased	0.5	
Approximate weight			2	g
			0.07	oz.
Mounting torque	minimum		6 (5)	kgf · cm (lbf · in)
	maximum		12 (10)	
Marking device		Case style TO-220AB	12TTS08H	

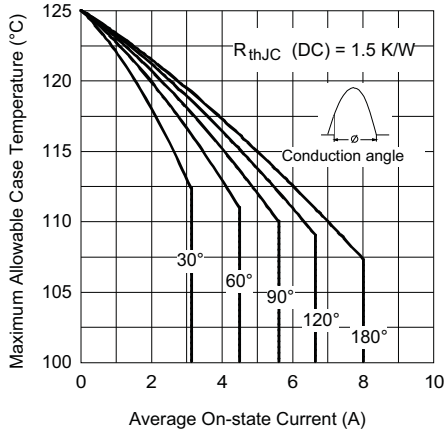


Fig. 1 - Current Rating Characteristics

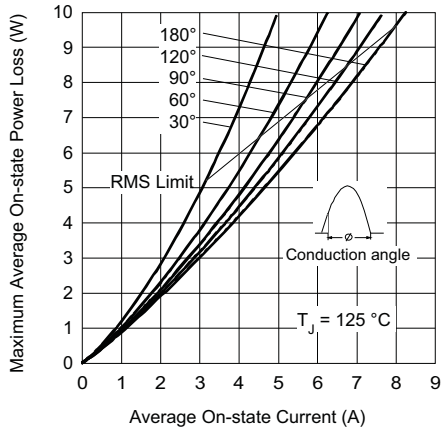


Fig. 3 - On-State Power Loss Characteristics

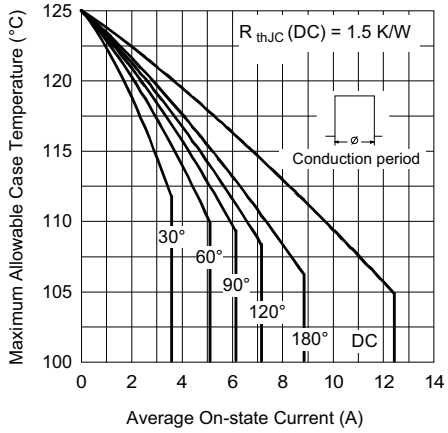


Fig. 2 - Current Rating Characteristics

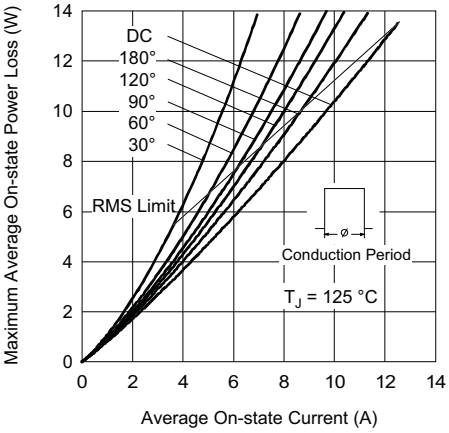


Fig. 4 - On-State Power Loss Characteristics

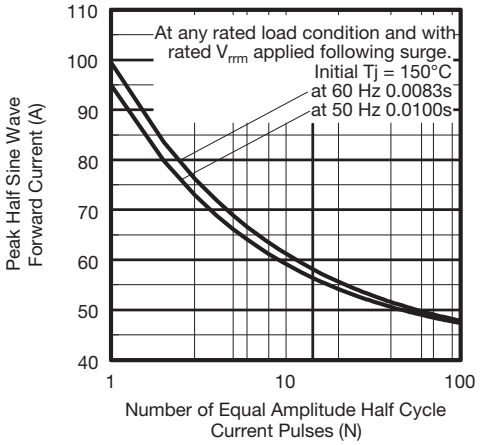


Fig. 5 - Maximum Non-Repetitive Surge Current

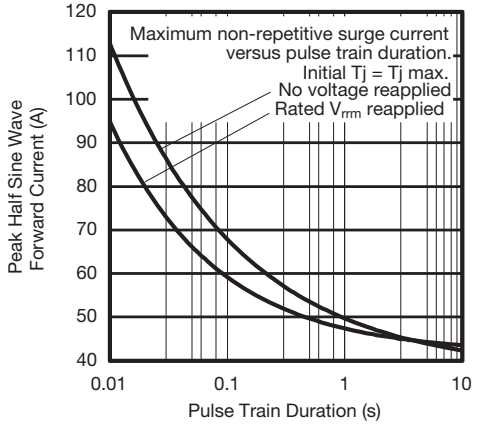


Fig. 6 - Maximum Non-Repetitive Surge Current

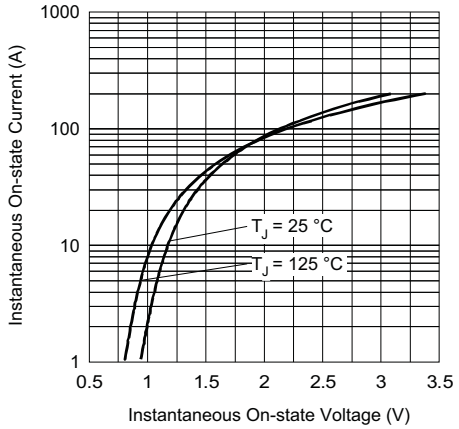


Fig. 7 - On-State Voltage Drop Characteristics

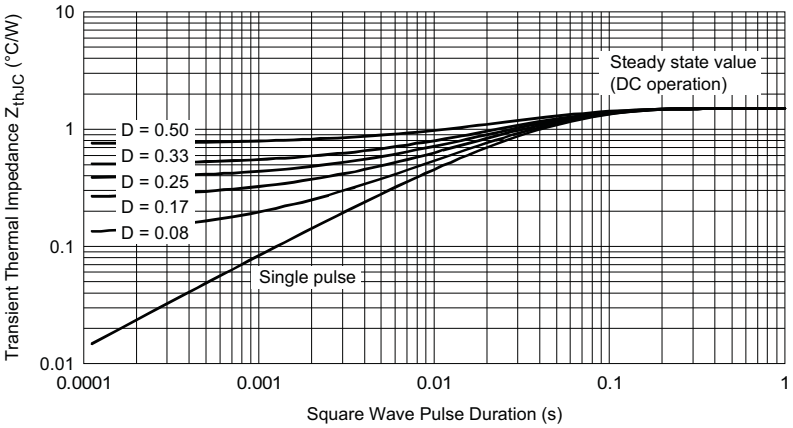
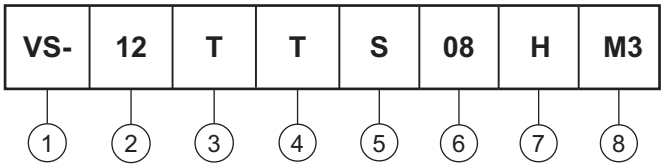


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics

ORDERING INFORMATION TABLE

Device code



1 - Vishay Semiconductors product

2 - Current rating (12.5 A)

3 - Circuit configuration:
T = single thyristor

4 - Package:
T = TO-220

5 - Type of silicon:
S = standard recovery rectifier

6 - Voltage rating (08 = 800 V)

7 - H = AEC-Q101 qualified

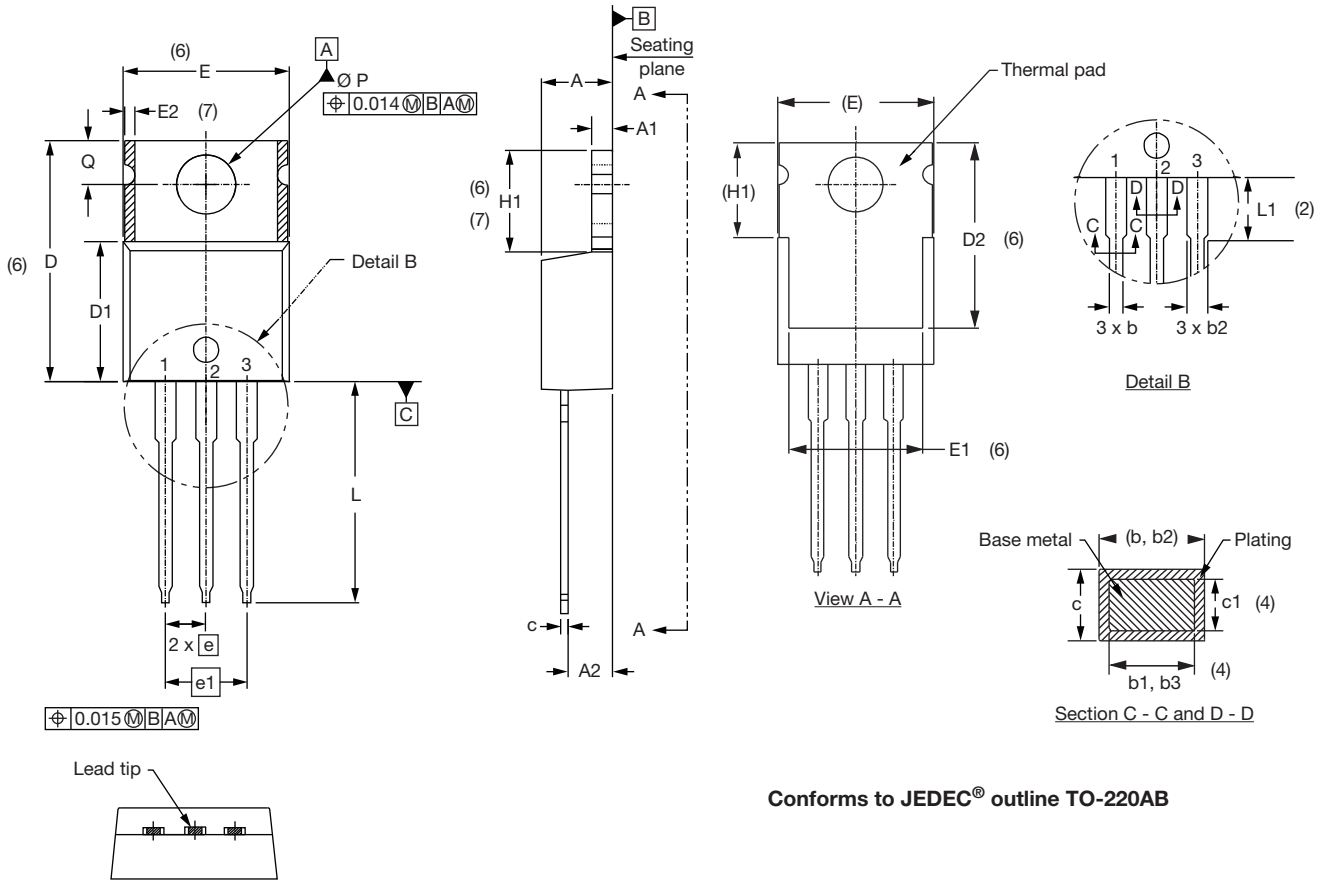
8 - Environmental digit:
M3 = halogen-free, RoHS-compliant, and terminations lead (Pb)-free

ORDERING INFORMATION (Example)			
PREFERRED P/N	**QUANTITY PER T/R**	**MINIMUM ORDER QUANTITY**	**PACKAGING DESCRIPTION**
VS-12TTS08HM3	50	1000	Antistatic plastic tube

LINKS TO RELATED DOCUMENTS	
Dimensions	www.vishay.com/doc?95222
Part marking information	www.vishay.com/doc?95028

TO-220AB

DIMENSIONS in millimeters and inches



Conforms to JEDEC® outline TO-220AB

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	4.25	4.65	0.167	0.183	
A1	1.14	1.40	0.045	0.055	
A2	2.56	2.92	0.101	0.115	
b	0.69	1.01	0.027	0.040	
b1	0.38	0.97	0.015	0.038	4
b2	1.20	1.73	0.047	0.068	
b3	1.14	1.73	0.045	0.068	4
c	0.36	0.61	0.014	0.024	
c1	0.36	0.56	0.014	0.022	4
D	14.85	15.25	0.585	0.600	3
D1	8.38	9.02	0.330	0.355	
D2	11.68	12.88	0.460	0.507	6

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
E	10.11	10.51	0.398	0.414	3, 6
E1	6.86	8.89	0.270	0.350	6
E2	-	0.76	-	0.030	7
e	2.41	2.67	0.095	0.105	
e1	4.88	5.28	0.192	0.208	
H1	5.84	6.86	0.230	0.270	6, 7
L	13.52	14.02	0.532	0.552	
L1	3.32	3.82	0.131	0.150	2
Ø P	3.54	3.73	0.139	0.147	
Q	2.60	3.00	0.102	0.118	
θ	90° to 93°		90° to 93°		

Notes

(1) Dimensioning and tolerancing as per ASME Y14.5M-1994

(2) Lead dimension and finish uncontrolled in L1

(3) Dimension D, D1 and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body

(4) Dimension b1, b3 and c1 apply to base metal only

(5) Controlling dimensions: inches

(6) Thermal pad contour optional within dimensions E, H1, D2 and E1

(7) Dimensions E2 x H1 define a zone where stamping and singulation irregularities are allowed

(8) Outline conforms to JEDEC® TO-220, except A2 (maximum) and D2 (minimum) where dimensions are derived from the actual package outline

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